

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently amended): A light-emitting diode, comprising
 - a semiconductor layer structure including a substrate and at least one light-generating layer formed on said substrate and one transparent current-spreading layer deposited on said light-generating layer,
 - a first electrical contact layer on the back of said substrate, and
 - a second electrical contact layer ~~[[disposed]]~~ directly deposited on said current-spreading layer,

[[characterized in that]] wherein

 - the top surface of said current-spreading layer has vertical structuring to improve the decoupling of light, and
 - said second electrical contact layer has a lateral structure by means of which substantially uniform coupling of the electrical current into said current-spreading layer can be achieved.
2. (Previously presented): The light-emitting diode as described in claim 1, characterized in that
 - said second electrical contact layer is a central contact surface and, arranged about said central contact surface, a contact structure that is rotationally symmetrical with respect to the center point of said central contact surface and is composed of relatively narrow contact webs and/or contact points.

3. (Previously presented): The light-emitting diode as described in claim 2, characterized in that

- the rotational symmetry is a symmetry represented by a whole number.

4. (Previously presented): The light-emitting diode as described in claim 1, characterized in that said second electrical contact layer is realized as continuous.

5. (Previously presented): The light-emitting diode as described in claim 1, characterized in that

- said second electrical contact layer is discontinuous and is interconnected by a layer of transparent, light-conducting material.

6. (Previously presented): The light-emitting diode as described in claim 1, characterized in that said second electrical contact layer is arranged on structured and/or unstructured portions of said current-spreading layer.

7. (Previously Presented): The light-emitting diode as described in claim 1, characterized in that

- the vertical structuring is in the form of n-sided ($n > 3$) pyramids or frusta of pyramids cones or frusta of cones.

8. (Previously presented): A method for fabricating a light-emitting diode as described in claim 1, characterized in that

- a light-generating layer and thereafter a relatively thick and transparent current-spreading layer are deposited on a substrate and the back of said substrate is provided with a first electrical contact layer,

- vertical structuring to improve the decoupling of light is produced in the surface of said current-spreading layer,

- a second electrical contact layer having the desired lateral structure is deposited on the structured top surface of said current-spreading layer.

9. (Previously presented): The method for fabricating a light-emitting diode as described in claim 1, characterized in that

- a light-generating layer and thereafter a relatively thick and transparent current-spreading layer are deposited on a substrate and the back of said substrate is provided with a first electrical contact layer,

- a second electrical contact layer having the desired lateral structure is deposited on the top surface of said current-spreading layer, and

- vertical structuring to improve the decoupling of light is produced in the top surface of said current-spreading layer outside the areas of said second electrical contact layer.

10. (Previously presented): The light emitting diode of claim 2 wherein said central contact surface is a circular contact surface.

11. (Previously presented): The light emitting diode of claim 2 wherein said central contact surface is a square contact surface.

12. (Previously presented): The light emitting diode of claim 3 wherein said rotational symmetry matches the rotational symmetry of the light-emitting diode.

13. (Previously presented): The light emitting diode of claim 7 wherein said n-sided ($n > 3$) pyramids or frusta of pyramids, cones or frusta of cones are regularly arranged.

14. (Currently amended): A light-emitting diode, comprising

- a semiconductor layer structure including a substrate and at least one light-generating layer formed on said substrate and one transparent current-spreading layer deposited on said light-generating layer,

- a first electrical contact layer on the back of said substrate, and
- a second electrical contact layer ~~[[disposed]]~~ directly deposited on said current-spreading layer,

~~[[characterized in that]]~~ wherein

- the top surface of said current-spreading layer has vertical structuring to improve the decoupling of light, and

-said second electrical contact layer has a lateral structure by means of which substantially uniform coupling of the electrical current into said current-spreading layer can be achieved,

wherein said second electrical contact layer has a lateral structure with a circumferential contact web arranged about a central contact structure.

15. (Previously Presented): The light-emitting diode as described in claim 1, characterized in that

- the vertical structuring is in the form of cones or frusta of cones.

16. (Previously Presented): The light emitting diode of claim 15 wherein said cones or frusta of cones are regularly arranged.

17. (New) The light emitting diode of claim 1 wherein said lateral structure of said contact layer extends over and directly contacts said vertical structuring of said current-spreading layer.

18. (New) The light emitting diode of claim 14 wherein said lateral structure of said contact layer extends over and directly contacts said vertical structuring of said current-spreading layer.

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